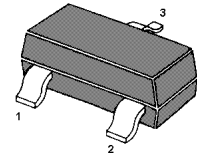


MMBTSD1304

NPN Silicon Epitaxial Planar Transistor

Audio muting application.



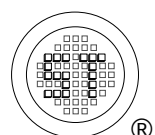
1. Base 2. Emitter 3. Collector
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	25	V
Collector Emitter Voltage	V_{CEO}	20	V
Emitter Base Voltage	V_{EBO}	12	V
Collector Current	I_C	300	mA
Base Current	I_B	30	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 2\text{ V}$, $I_C = 4\text{ mA}$	$h_{FE(For)}$ $h_{FE(Rev)}$	200 20	- -	800 -	- -
Collector Base Cutoff Current at $V_{CB} = 25\text{ V}$	I_{CBO}	-	-	100	nA
Emitter Base Cutoff Current at $V_{EB} = 12\text{ V}$	I_{EBO}	-	-	100	nA
Collector Emitter Saturation Voltage at $I_C = 100\text{ mA}$, $I_B = 10\text{ mA}$	$V_{CE(sat)}$	-	-	0.25	V
Base Emitter Saturation Voltage at $I_C = 100\text{ mA}$, $I_B = 10\text{ mA}$	$V_{BE(sat)}$	-	-	1	V
Collector Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	10	-	pF
Gain Bandwidth Product at $V_{CE} = 10\text{ V}$, $I_C = 1\text{ mA}$	f_T	-	60	-	MHz



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